



STPS6045CP/CPI/CW

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2x30 A
V_{RRM}	45 V
$T_j(\text{max})$	175 °C
$V_F(\text{max})$	0.63 V

FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREME FAST SWITCHING
- LOW THERMAL RESISTANCE
- INSULATED PACKAGE: TOP-3I
Insulating voltage = 2500V_{RMS}
Capacitance = 12pF

DESCRIPTION

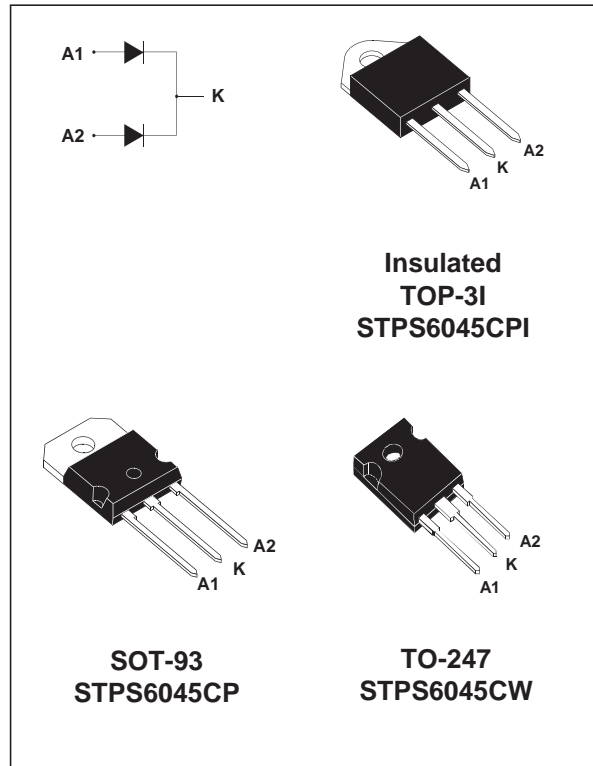
Dual center tap Schottky rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged either in SOT-93, TOP-3I or TO-247, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit	
V_{RRM}	Repetitive peak reverse voltage			45	V	
$I_{F(RMS)}$	RMS forward current			60	A	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	SOT-93 TO-247	$T_c = 150^\circ\text{C}$	Per diode	30	A
		TOP-3I	$T_c = 130^\circ\text{C}$	Per device	60	
I_{FSM}	Surge non repetitive forward current		$t_p = 10 \text{ ms}$ sinusoidal	400	A	
I_{RRM}	Repetitive Peak reverse current		$t_p = 2 \mu\text{s}$ square $F = 1\text{kHz}$	1	A	
I_{RSM}	Non repetitive peak reverse current		$t_p = 100 \mu\text{s}$ square	3	A	
T_{stg}	Storage temperature range			- 65 to + 175	°C	
T_j	Maximum operating junction temperature *			175	°C	
dV/dt	Critical rate of rise of reverse voltage			10000	V/ μs	

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink



THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case	SOT-93 / TO-247	Per diode Total	°C/W
		TOP-3I	Per diode Total	
R _{th(c)}		SOT-93 / TO-247	Coupling	0.15
		TOP-3I		0.4

When the diodes 1 and 2 are used simultaneously:
 $\Delta T_J(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)} (\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = V _{RRM}			500	μA
		T _j = 125°C			20	80	mA
V _F *	Forward voltage drop	T _j = 125°C	I _F = 30 A		0.53	0.63	V
		T _j = 25°C	I _F = 60 A			0.84	
		T _j = 125°C	I _F = 60 A		0.68	0.78	

Pulse test : ** tp = 380 μs, δ < 2%
 To evaluate the conduction losses use the following equation:
 $P = 0.48 \times I_{F(AV)} + 0.005 I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

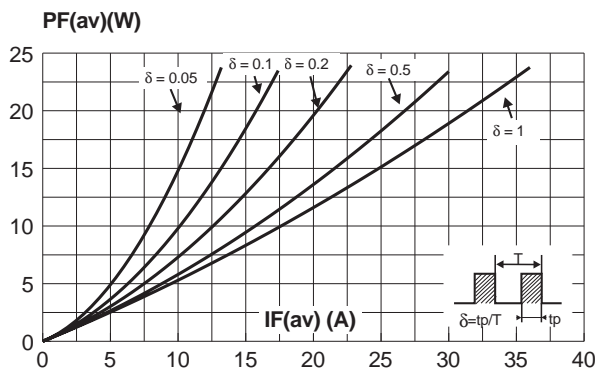


Fig. 2: Average current versus ambient temperature (δ=0.5, per diode).

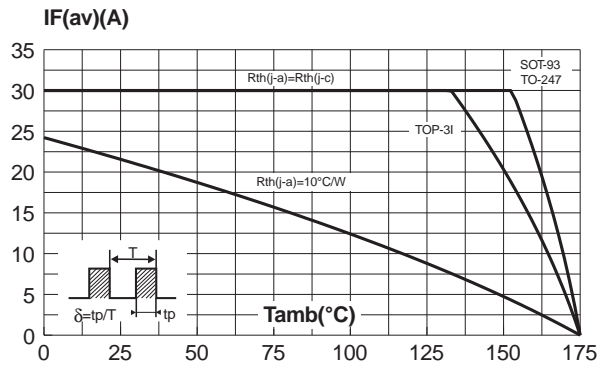


Fig. 3-1: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (SOT-93 and TO-247).

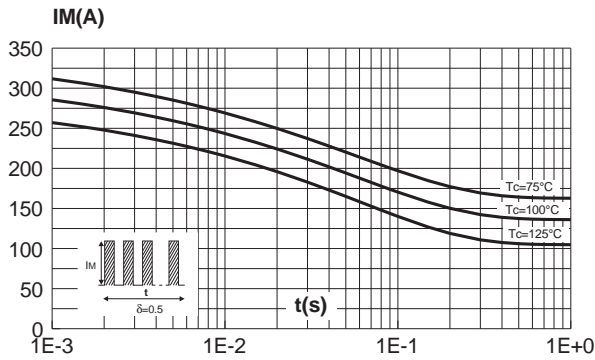


Fig. 4: Relative variation of thermal transient impedance junction to case versus pulse duration.

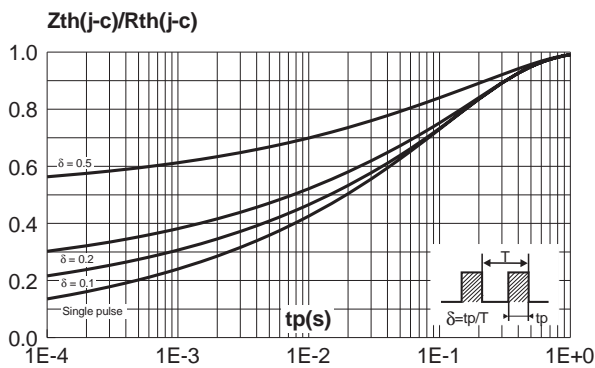


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).

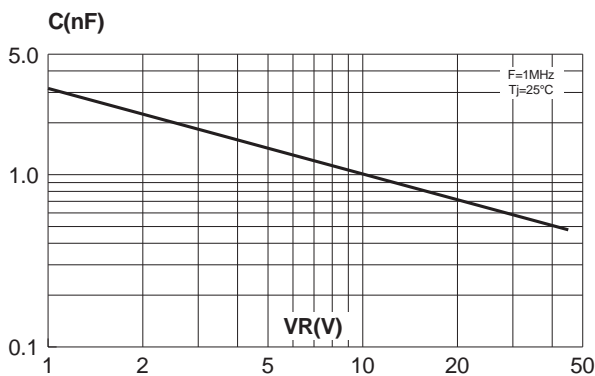


Fig. 3-2: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (TOP-3I).

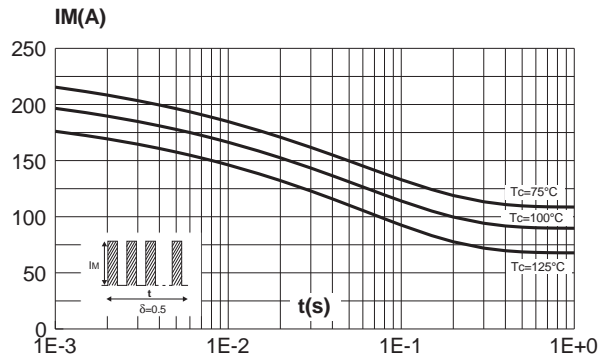


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

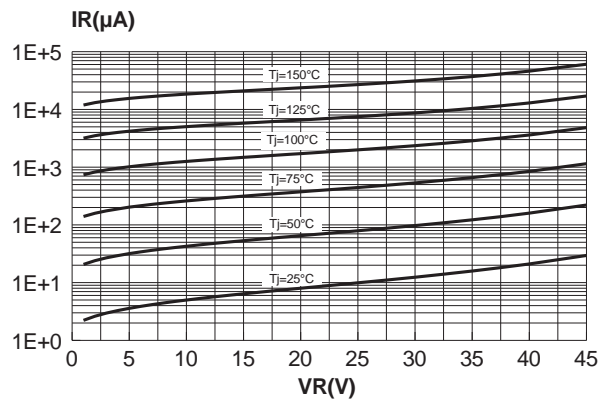
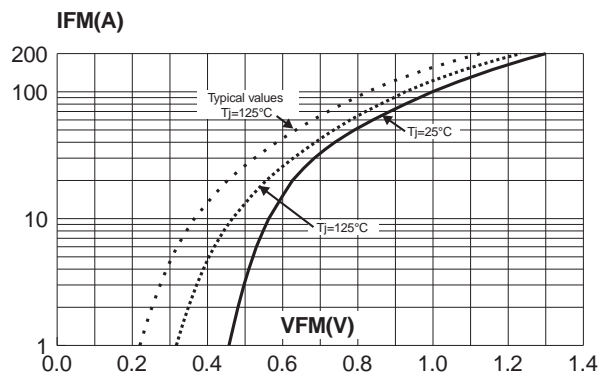
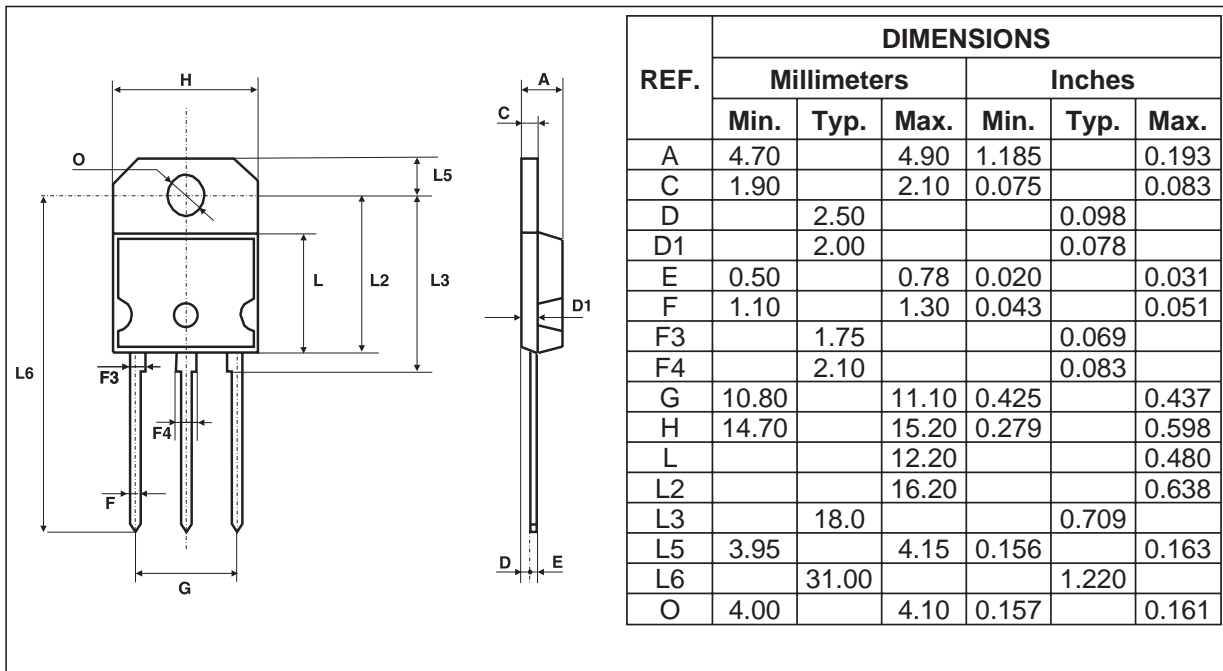


Fig. 7: Forward voltage drop versus forward current (maximum values, per diode).

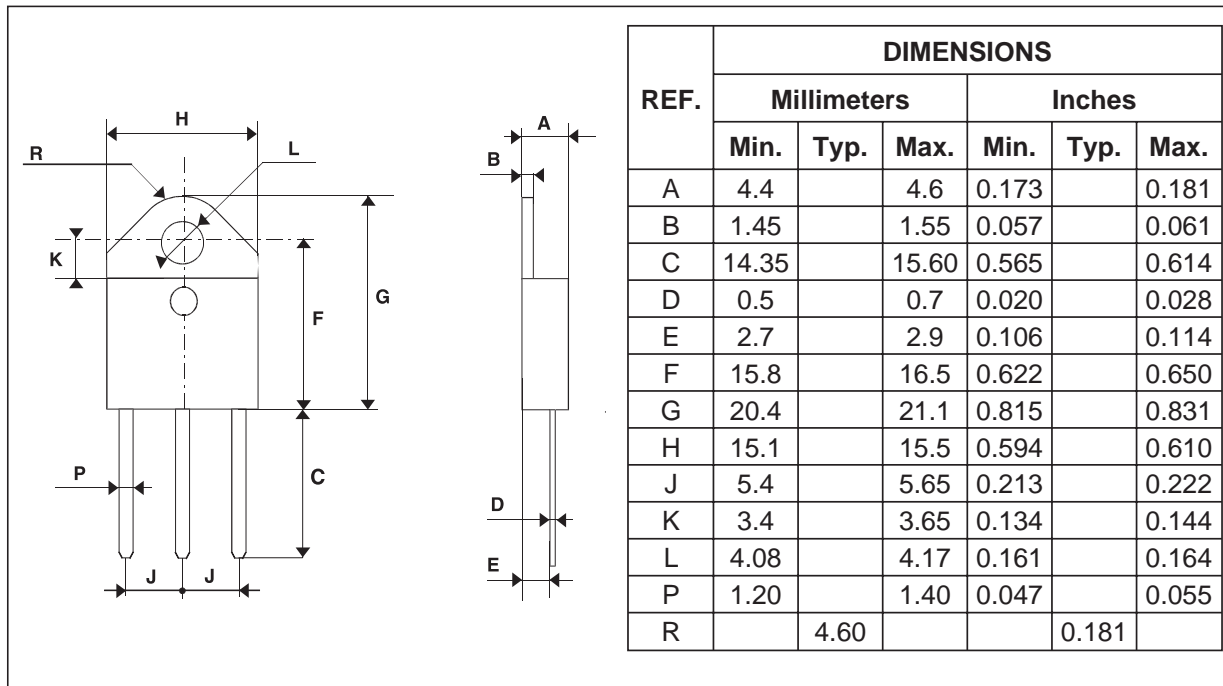


STPS6045CP/CPI/CW

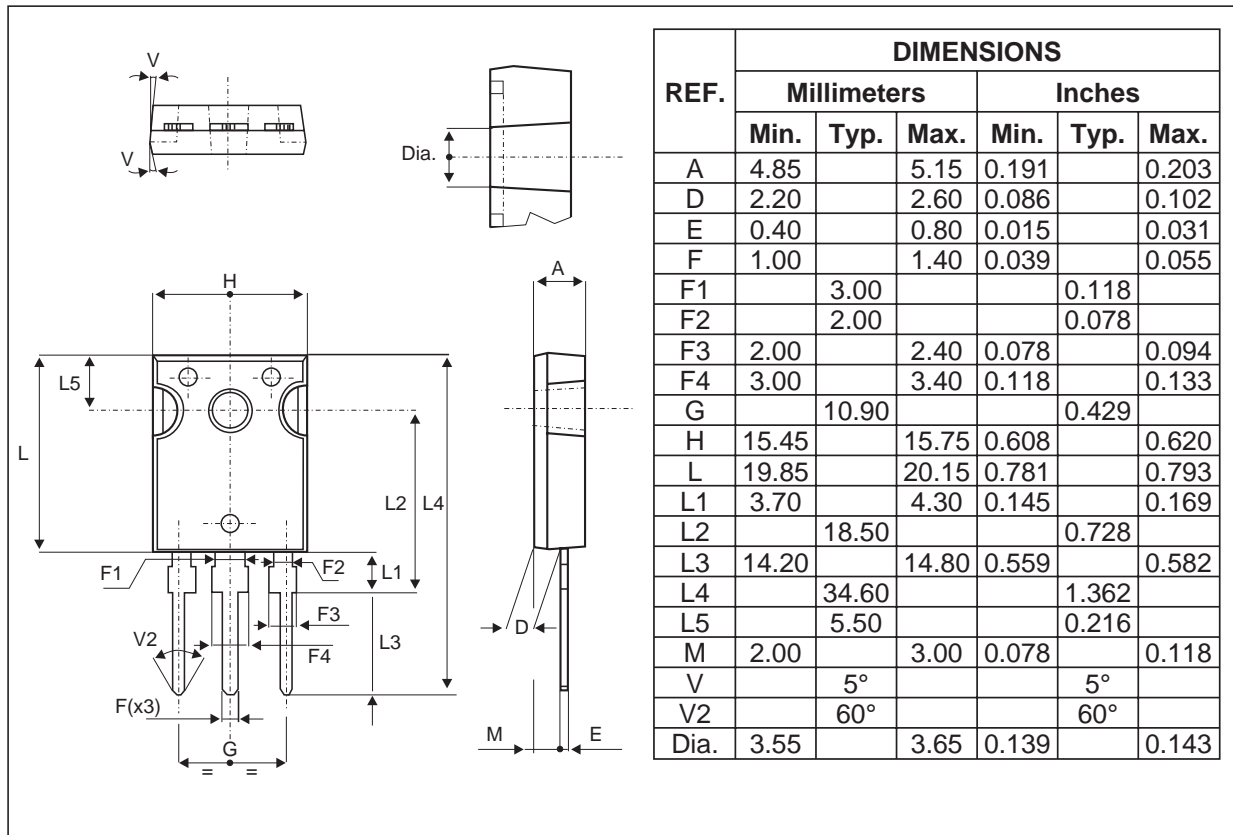
PACKAGE MECHANICAL DATA
SOT-93



PACKAGE MECHANICAL DATA
TOP-3I (isolated)



PACKAGE MECHANICAL DATA
TO-247



Type	Marking	Package	Weight	Base qty	Delivery mode
STPS6045CP	STPS6045CP	SOT-93	3.97 g.	30	Tube
STPS6045CPI	STPS6045CPI	TOP-3I	4.46 g.	120	Bulk
STPS6045CW	STPS6045CW	TO-247	4.36 g.	30	Tube

- Cooling method: by conduction (C)
- Recommended torque value: 0.8 N.m.
- Maximum torque value: 1.0 N.m.
- Epoxy meets UL94,V0

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